

FGL60N100BNTD;ON-Semiconductor; Tranzystor IGBT;TO264;42A;1kV;72W



Dane techniczne:

Nazwa: FGL60N100BNTD Typ: tranzystor IGBT Napięcie kolektor-emiter: 1000V Prąd kolektora: 42A Moc rozpraszana: 72W Obudowa: TO264 Montaż: THT Producent: ON-Semiconductor

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March 2014



FGL60N100BNTD 1000 V, 60 A NPT Trench IGBT

Features

- · High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.5 V @ I_C = 60 A
- High Input Impedance
- Built-in Fast Recovery Diode

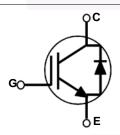
Applications

· UPS, Welder



Using Fairchild's proprietary trench design and advanced NPT technology, the 1000V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device offers the optimum performance for hard switching application such as UPS, welder applications.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		1000	V
V _{GES}	Gate to Emitter Voltage		± 25	V
	Collector Current	@ T _C = 25°C	60	А
I _C Collecto	Collector Current	@ T _C = 100 ^o C	42	A
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	200	A
I _F	Diode Continuous Forward Current	@ T _C = 100 ^o C	15	A
P _D	Maximum Power Dissipation	@ T _C = 25°C	180	W
	Maximum Power Dissipation	@ T _C = 100°C	72	W
TJ	Operating Junction Temperature	-55 to +150	°C	
T _{stg}	Storage Temperature Range	-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	300	°C	

Notes: 1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R _{0JC} (IGBT) Thermal Resistance, Junction to Case		0.69	°C/W
R _{0JC} (Diode) Thermal Resistance, Junction to Case		2.08	°C/W
R _{0JA} Thermal Resistance, Junction to Ambient		25	°C/W

· ·		Top Mark	Packag	ge Packing Method		Re	el Size	Tape Width		Quantity	
		TO-264	54 Tube			N/A	N/A		30		
Electric	al Cha	aracteristics o	f the IG	BB.	T _C = 25°C unless otherwise	noted					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max	. Unit	
Off Charac	teristics						-				
BV _{CES}	Collecto	r to Emitter Breakdow	n Voltage	V _{GE}	= 0 V, I _C = 1 mA		1000	-	-	V	
I _{CES}	Collecto	r Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0 V$		-	-	1	mA		
I _{GES}	G-E Lea	akage Current		V _{GE}	$_{\rm E}$ = V _{GES} , V _{CE} = 0 V		-	-	±500	nA	
On Charac	teristics										
V _{GE(th)}	G-E Threshold Voltage		I _C = 60 mA, V _{CE} = V _{GE}		4.0	5.0	7.0	V			
			I _C =10 A, V _{GE} = 15 V		-	1.5	1.8	V			
V _{CE(sat)}	Collector to Emitter Saturation Voltage		I _C = 60 A, V _{GE} = 15 V,		-	2.5	2.9	V			
Dynamic C	haracter	istics						_+	+		
C _{ies}	Input Capacitance Output Capacitance		V _{CE} = 10 V, V _{GE} = 0 V, f = 1MHz		- 1	6000	-	pF			
C _{oes}					-	260	-	pF			
C _{res}	Reverse	e Transfer Capacitance	ice				-	200	-	pF	
Switching	Characte	ristics									
t _{d(on)}	Turn-On	Delay Time					-	140	-	ns	
r	Rise Tin	ne		$V_{CC} = 600 \text{ V}, \text{ I}_{C} = 60 \text{ A},$ $R_{G} = 51 \Omega, \text{ V}_{GE} = 15 \text{ V},$ Inductive Load, T _C = 25°C			-	320	-	ns	
t _{d(off)}	Turn-Of	f Delay Time				-	630	-	ns		
ŀf	Fall Tim	e					-	130	-	ns	
Qg	Total Ga	ate Charge		. ,			-	275	-	nC	
Q _{ge}	Gate to	Emitter Charge			= 600 V, I _C = 60 A, = 15 V, T _C = 25°C		-	45	-	nC	
Q _{gc}	Gate to	Collector Charge		$\sim _{\rm GE} = 15$ v, $1_{\rm C} = 25$ C			-	95	-	nC	

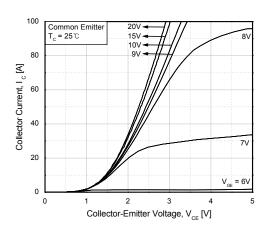
Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

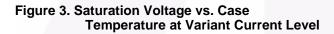
Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 15 A	-	1.2	1.7	V
		I _F = 60 A	-	1.8	2.1	V
t _{rr}	Diode Reverse Recovery Time	I _F = 60 A, di/dt = 20 A/us	-	1.2	1.5	us
I _R	Instantaneous	V _{RRM} = 1000 V	-	0.05	2.0	uA

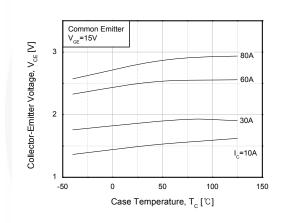
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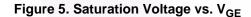
Typical Performance Characteristics

Figure 1. Typical Output Characteristics









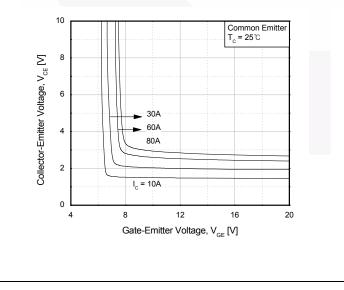
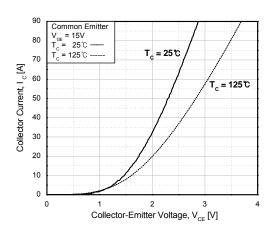
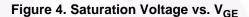


Figure 2. Typical Saturation Voltage Characteristics





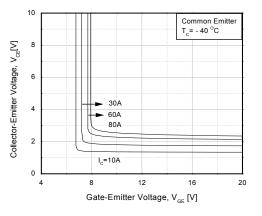
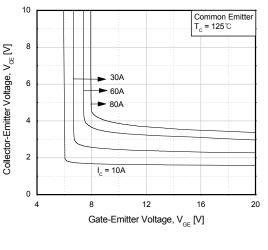


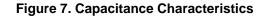
Figure 6. Saturation Voltage vs. V_{GE}

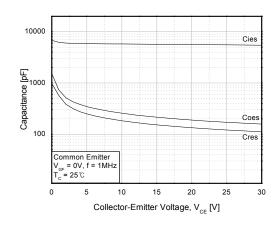


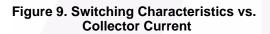
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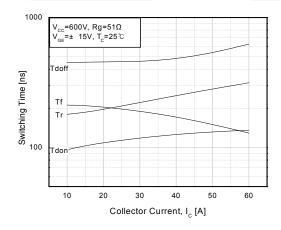
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Typical Performance Characteristics











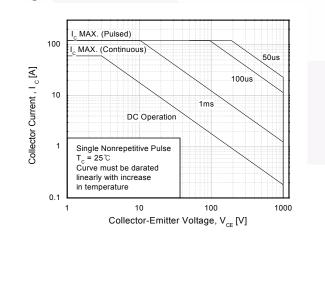


Figure 8. Switching Loss vs. Gate Resistance

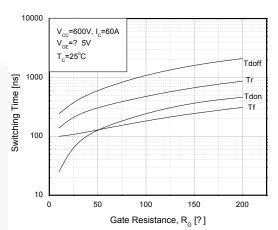
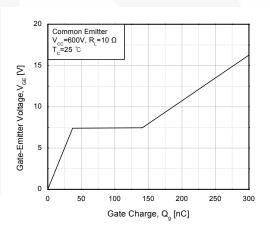
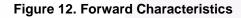
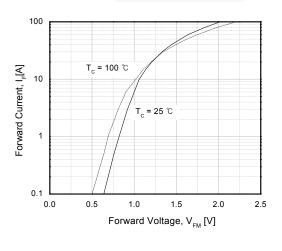
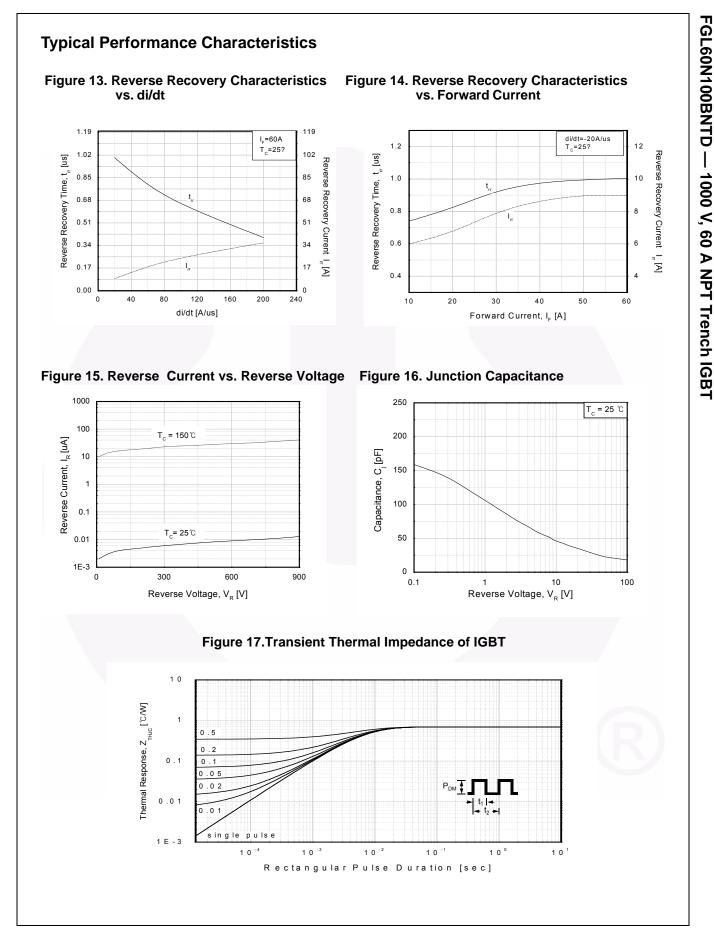


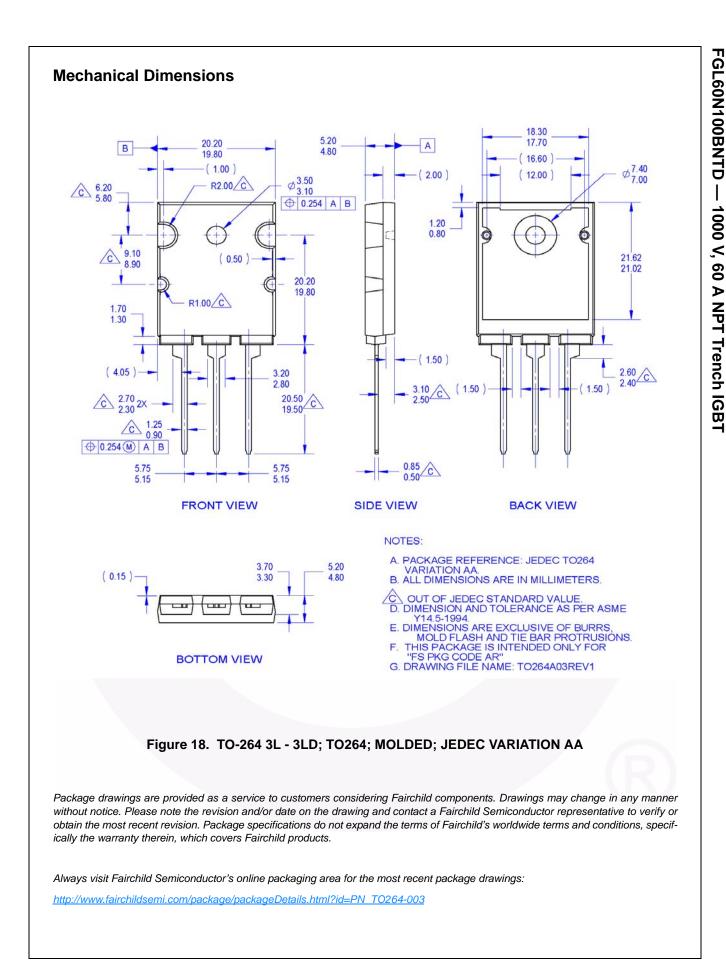
Figure 10. Gate Charge Characteristics













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